



SD2918

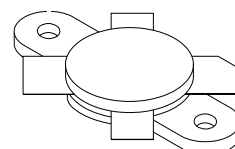
RF POWER TRANSISTORS HF/VHF/UHF N-CHANNEL MOSFETs

ADVANCE DATA

- GOLD METALLIZATION
- EXCELLENT THERMAL STABILITY
- COMMON SOURCE CONFIGURATION
- $P_{out} = 30\text{ W}$ MIN. WITH 18 dB GAIN @ 30 MHz

DESCRIPTION

The SD2918 is a gold metallized N-Channel MOS field-effect RF power transistor. It is intended for use in 50 V DC large signal applications up to 200 MHz



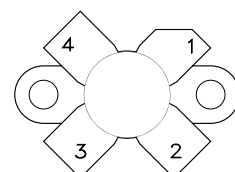
M113

epoxy sealed

ORDER CODE
SD2918

BRANDING
TSD2918

PIN CONNECTION



PC12230

- | | |
|-----------|-----------|
| 1. Drain | 3. Gate |
| 2. Source | 4. Source |

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25\text{ }^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
$V_{(BR)DSS}$	Drain Source Voltage	125	V
V_{DGR}	Drain-Gate Voltage ($R_{GS} = 1\text{ M}\Omega$)	125	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current	6	A
P_{DISS}	Power Dissipation	175	W
T_j	Max. Operating Junction Temperature	200	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	-65 to 150	$^{\circ}\text{C}$

THERMAL DATA

$R_{th(j-c)}$	Junction-Case Thermal Resistance	1.0	$^{\circ}\text{C/W}$
$R_{th(c-s)}$	Case-Heatsink Thermal Resistance *	0.30	$^{\circ}\text{C/W}$

* Determined using a flat aluminum or copper heatsink with thermal compound applied (Dow Corning 340 or equivalent).

ELECTRICAL SPECIFICATION (T_{case} = 25 °C)

STATIC

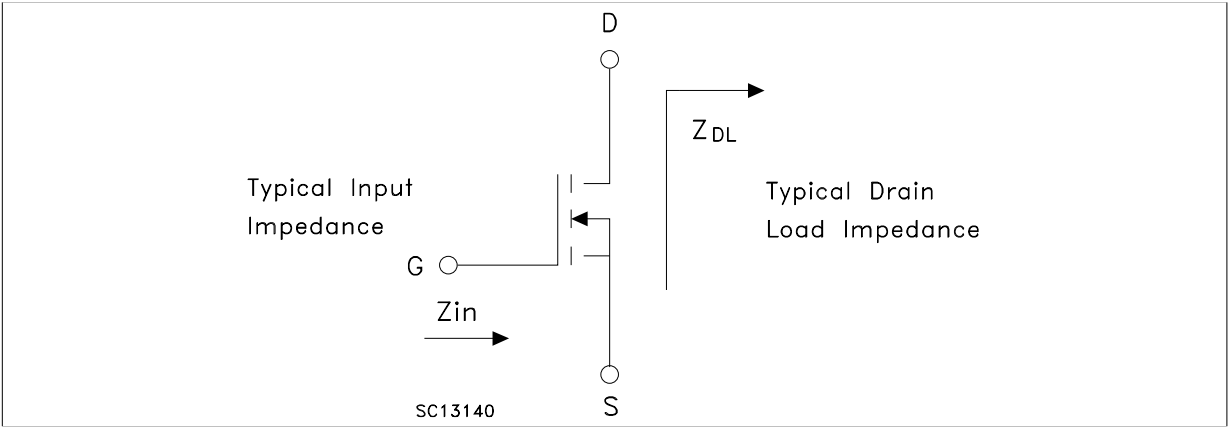
Symbol	Parameter			Min.	Typ.	Max.	Unit
V _{(BR)DSS}	V _{GS} = 0V	I _{DS} = 10 mA		125			V
I _{DSS}	V _{GS} = 0V	V _{DS} = 50 V				1.0	mA
I _{GSS}	V _{GS} = 20V	V _{DS} = 0 V				1	μA
V _{GS(Q)}	V _{DS} = 10V	I _D = 10 mA		1.0		5.0	V
V _{DS(ON)}	V _{GS} = 10V	I _D = 2.5 A				5.0	V
g _{FS}	V _{DS} = 10V	I _D = 2.5 A		0.8			mho
C _{ISS}	V _{GS} = 0V	V _{DS} = 50 V	f = 1 MHz		58		pF
C _{OSS}	V _{GS} = 0V	V _{DS} = 50 V	f = 1 MHz		35.5		pF
C _{RSS}	V _{GS} = 0V	V _{DS} = 50 V	f = 1 MHz		7.5		pF

REF. 1022497C

DYNAMIC

Symbol	Parameter				Min.	Typ.	Max.	Unit
P _{OUT}	f = 30MHz	V _{DD} = 50V	P _{in} = 0.475 W	I _{DQ} = 100 mA	30			W
G _{PS}	f = 30MHz	V _{DD} = 50V	P _{out} = 30 W	I _{DQ} = 100 mA	18	22		dB
η _D	f = 30MHz	V _{DD} = 50V	P _{out} = 30 W	I _{DQ} = 100 mA	50	55		%
Load Mismatch	f = 30MHz All Angles	V _{DD} = 50V	P _{out} = 30 W	I _{DQ} = 100 mA	30:1			VSWR

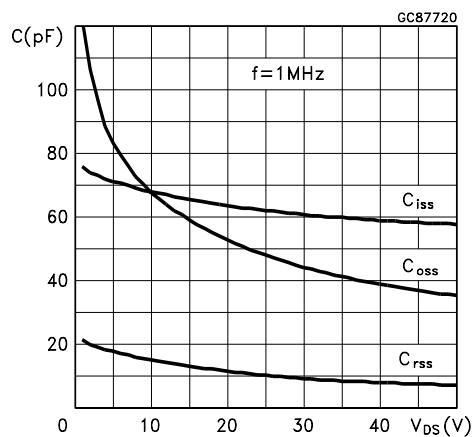
IMPEDANCE DATA



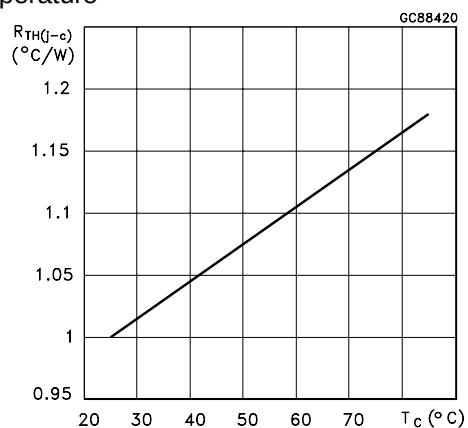
FREQ.	Z _{IN} (Ω)	Z _{DL} (Ω)
30 MHz	24.4 - j 13.4	28.8 + j 7.2

TYPICAL PERFORMANCE

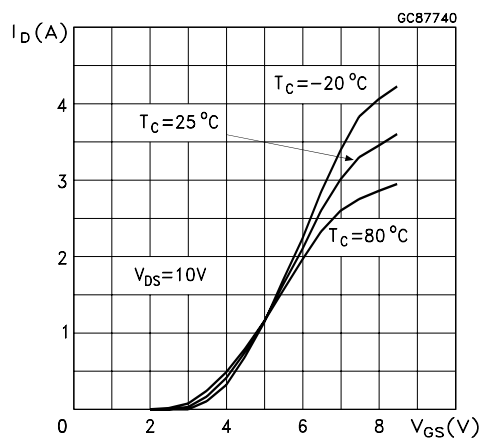
Capacitance vs Drain-Source Voltage



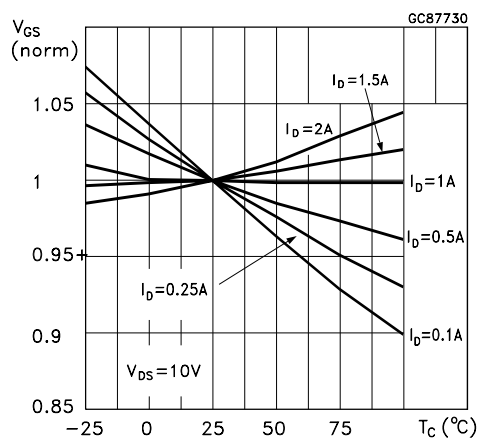
Maximum Thermal Resistance vs Case Temperature



Drain Current vs Gate Voltage

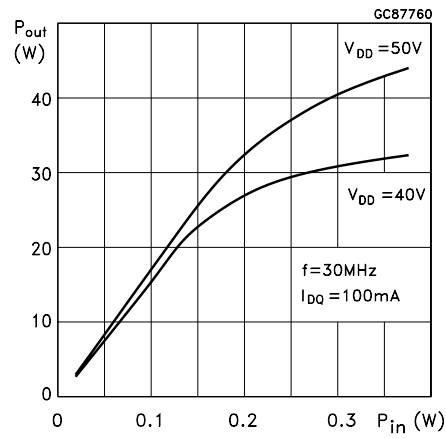


Gate-Source Voltages vs Case Temperature

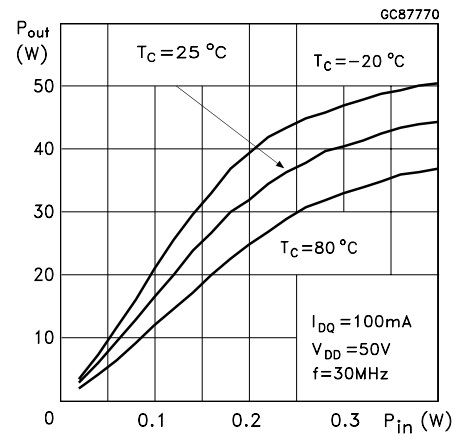


TYPICAL PERFORMANCE

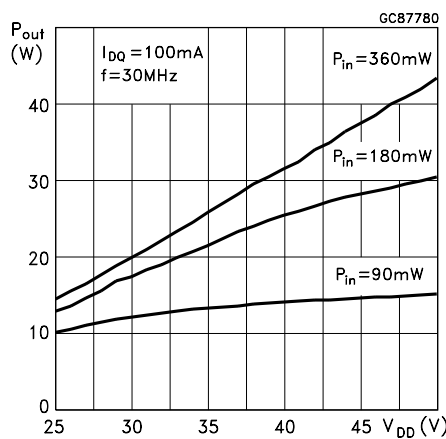
Output Power vs Input Power



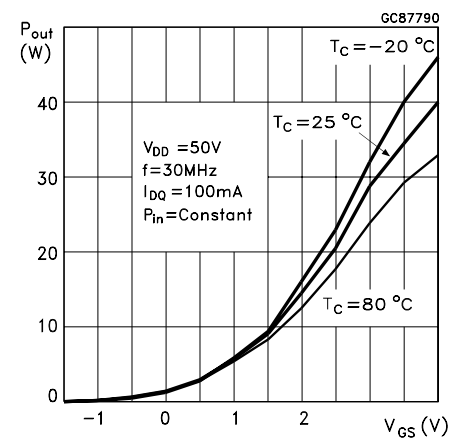
Output Power vs Input Power



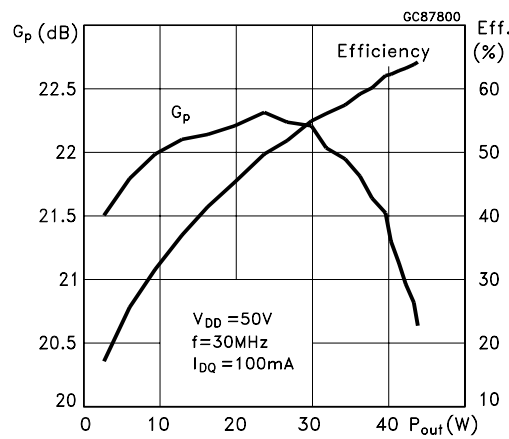
Output Power vs Voltage Supply



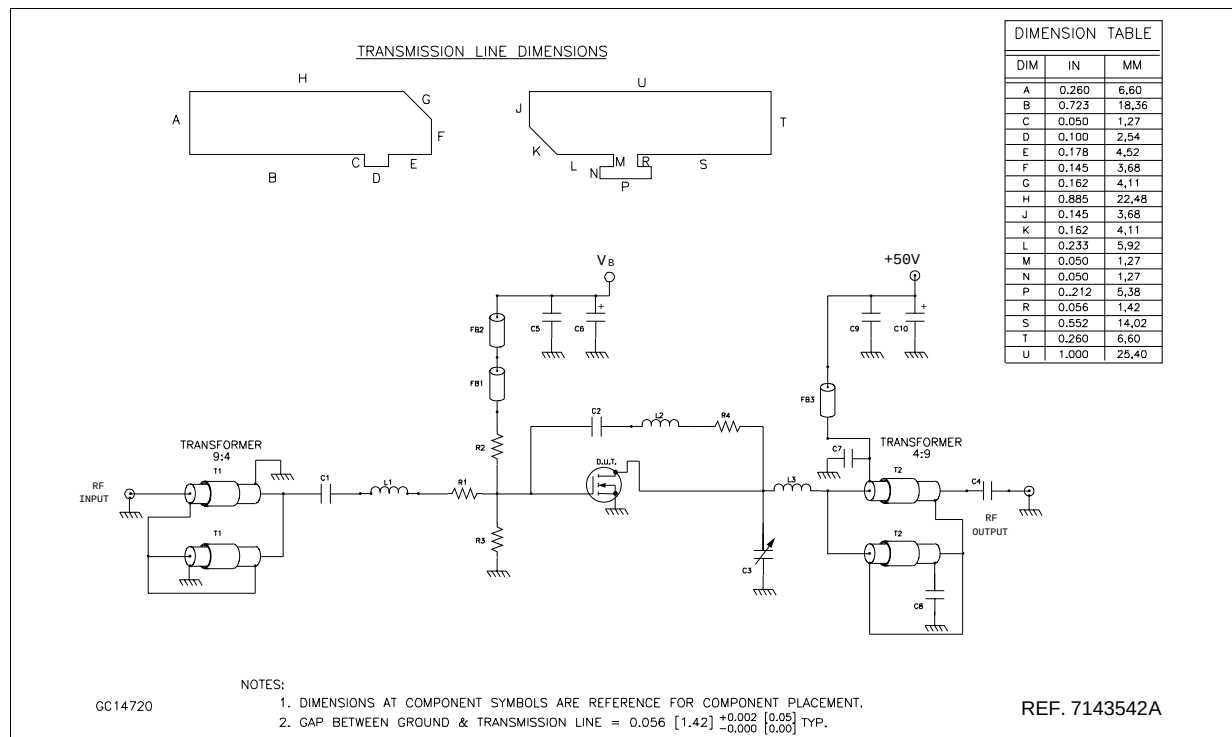
Output Power vs Gate Voltage



Power Gain & Efficiency vs Output Power



30 MHz Test Circuit Schematic



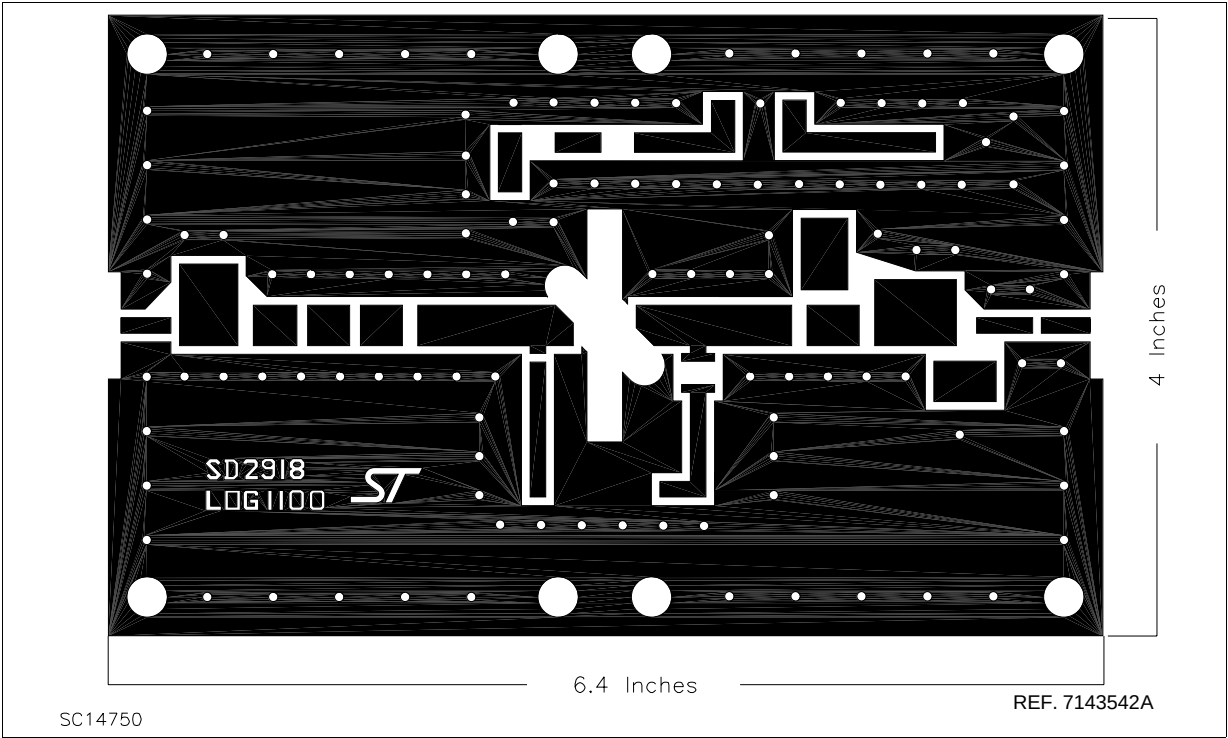
30 MHz Test Circuit Component Part List

R4	CR2512-1W-101JB	VENKEL	100 OHM, 1W SURFACE MOUNT CHIP RESISTOR
R3	29SJ901	XICON	160 OHM, 1W CARBON FILM AXIAL-LEAD RESISTOR
R2	29SJ901	XICON	160 OHM, 1W CARBON FILM AXIAL-LEAD RESISTOR
R1	CR2512-1W-3R9JT	VENKEL	3.9 OHM, 1W SURFACE MOUNT CHIP RESISTOR
FB3	2843000102	FAIR-RITE CORP.	MULTI-APERATURE CORE
FB2	2743021447	FAIR-RITE CORP.	SHIELD BEAD SURFACE MOUNT EMI
FB1	2743021447	FAIR-RITE CORP.	SHIELD BEAD SURFACE MOUNT EMI
L3	8073	BELDEN	INDUCTOR, 3 TURNS AIR WOUND #14AWG, ID=0.375[9.53], POLY COATED MAGNET WIRE
L2	1557	ALPHA	INDUCTOR, 7 TURNS AROUND SHIELD BEAD (PT# FAIR-RITE 2643801102) #16AWG HOOK UP WIRE.
L1	8073	BELDEN	INDUCTOR, 4 TURNS AIR WOUND #14AWG, ID=0.375[9.53], POLY COATED MAGNET WIRE
C10	SKA100M160	MALLORY	10μF/160V AXIAL-LEAD ALUMINIUM ELECTROLYTIC CAPACITOR
C9	C1812X7R501-103KNE	VENKEL	0.01μF/500V SURFACE MOUNT CERAMIC CHIP CAPACITOR
C8	C1812X7R501-103KNE	VENKEL	0.01μF/500V SURFACE MOUNT CERAMIC CHIP CAPACITOR
C7	C1812X7R501-103KNE	VENKEL	0.01μF/500V SURFACE MOUNT CERAMIC CHIP CAPACITOR
C6	RVS-50V100M-R	ELNA	10μF/50V VERTICAL SURFACE MOUNT CHIP ALUMINUM ELECTROLYTIC CAPACITOR
C5	C1812X7R501-103KNE	VENKEL	0.01μF/500V SURFACE MOUNT CERAMIC CHIP CAPACITOR
C4	ATC200B103KW50X	ATC	10000pF ATC 200B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C3	463	ARCO	20-180pF TYPE ST46 STANDARD 3 TURNS VARIABLE CAPACITOR
C2	ATC200B103KW50X	ATC	10000pF ATC 200B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C1	ATC200B103KW50X	ATC	10000pF ATC 200B SURFACE MOUNT CERAMIC CHIP CAPACITOR
T2			TRANSFORMER, 4:9 75.0 OHM, O.D. 0.090 1" LG. COAXIAL CABLE 5TURNS AROUND SHIELD BEAD (PT#2643801002 FAIR-RITE CORP.)
T1			TRANSFORMER, 9:4 75.0 OHM, O.D. 0.090 1" LG. COAXIAL CABLE 5TURNS AROUND SHIELD BEAD (PT#2643801002 FAIR-RITE CORP.)
PCB	GO300M1026	ROGERS CORP	WOVEN FIBERGLASS REINFORCED PTFE 0.030" THK, $\epsilon_r = 2.55$, 2 Oz ED Cu BOTH SIDES
COMPONENT	PART NO	VENDOR	DESCRIPTION

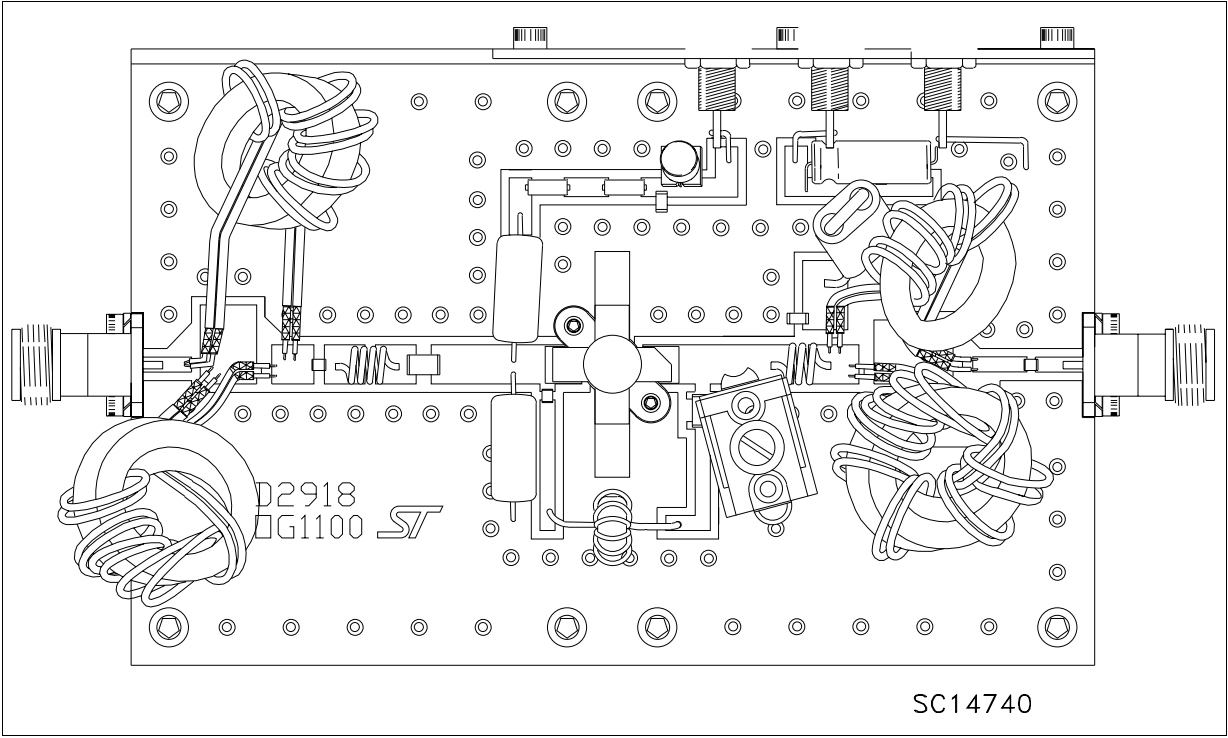
SC14730

SD2918

30 MHz Test Circuit Photomaster

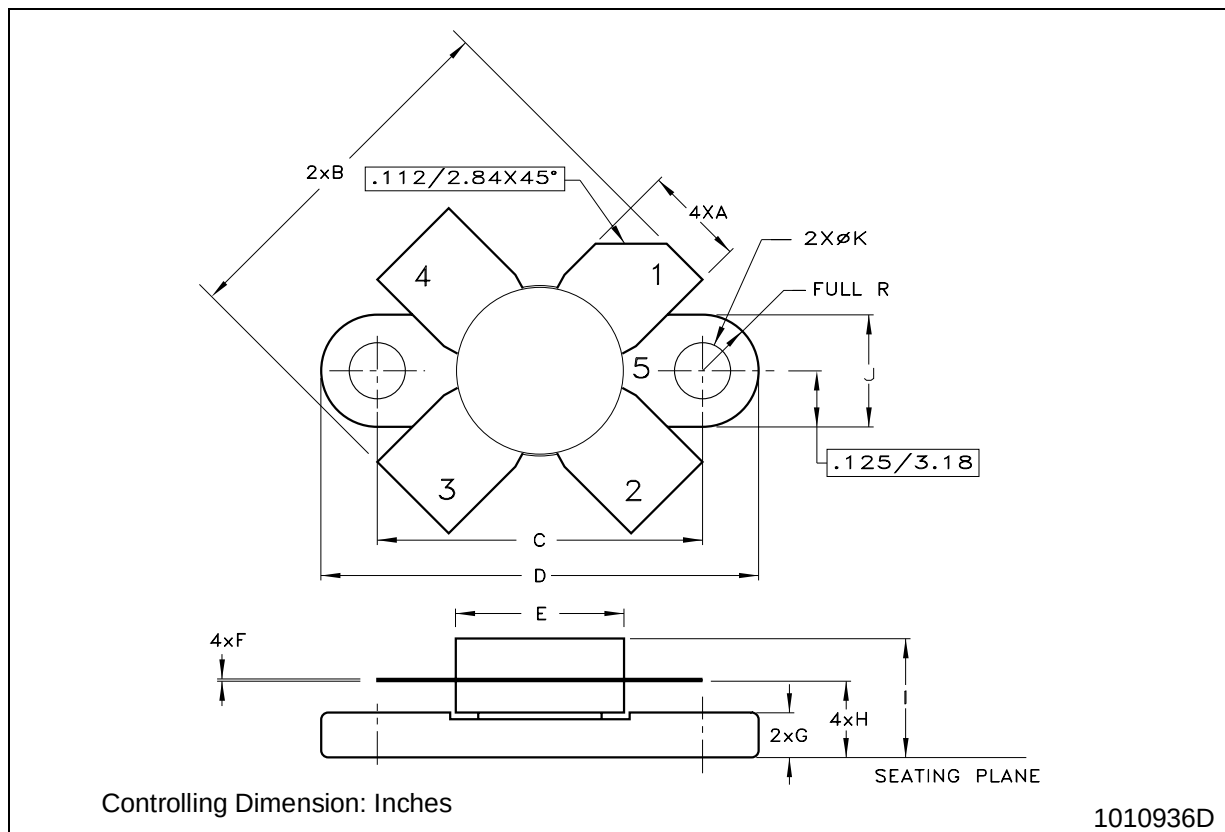


30 MHz Production Test Fixture



M113 (.380 DIA 4/L N/HERM W/FLG) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	5.59		5.84	0.220		0.230
B	19.81		20.83	0.780		0.820
C	18.29		18.54	0.720		0.730
D	24.64		24.89	0.970		0.980
E	9.40		9.78	0.370		0.385
F	0.10		0.15	0.004		0.006
G	2.16		2.67	0.085		0.105
H	4.06		4.57	0.160		0.180
I			7.14			0.281
J	6.22		6.48	0.245		0.255
K	3.05		3.30	0.120		0.130



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